

## SSCN3904GS8

## **NPN Switching Transistor**

### Features

VCB	VCE	VBE	VCESAT	IC
60	40V	6V	300mV	200mA

## > Description

The NPN Transistor is designed for use in linear and switching applications. The device is housed in the SOT-523 package, which is designed for telephony and professional communication equipment.

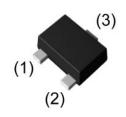
## Applications

- General purpose switching and amplification
- Telephony and professional communication equipment

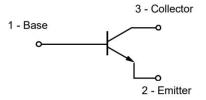
## > Ordering Information

Device	Package	Shipping
SSCN3904GS8	SOT-523	3000/Reel

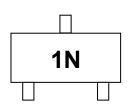
## > Pin configuration



**SOT-523** 



**Circuit Diagram** 



Marking(Top View)

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# ightarrow Absolute Maximum Ratings(T<sub>A</sub>=25°C unless otherwise noted)

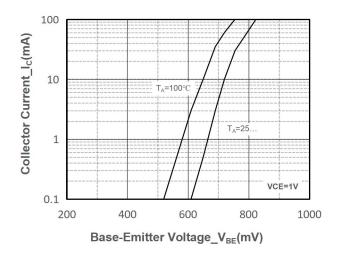
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector- Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current-Continuous	Ic	200	mA
Collector Power Dissipation	Pc	200	mW
Junction Temperature	TJ	150	$^{\circ}$
Storage Temperature	T <sub>STG</sub>	-55 to 150	$^{\circ}$

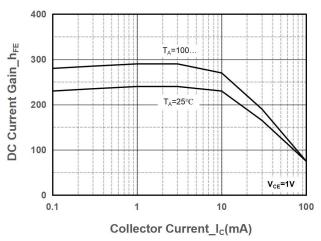
## ➤ Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	I <sub>C</sub> =10uA,I <sub>E</sub> =0	60			V
Collector-emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =1mA,I <sub>B</sub> =0	40			V
Emitter -Base Breakdown Voltage	BV <sub>EBO</sub>	I <sub>E</sub> =10uA,I <sub>C</sub> =0	6			V
Collector Cutoff Current	I <sub>CEX</sub>	V <sub>CE</sub> =30V, V <sub>EB</sub> =3V			50	nA
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =30V,I <sub>E</sub> =0			100	nA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =3V,I <sub>C</sub> =0			100	nA
		V <sub>CE</sub> =1V,I <sub>C</sub> =10mA	100		300	
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =1V,I <sub>C</sub> =0.1mA	40			
		V <sub>CE</sub> =1V,I <sub>C</sub> =100mA	30			
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =50mA,I <sub>B</sub> =5mA			0.3	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =50mA,I <sub>B</sub> =5mA			0.95	V
Transition frequency	f⊤	V <sub>CE</sub> =20V,I <sub>C</sub> =10mA	250			MHz
Transition requestoy	11	f=100MHz	200			IVII IZ
Delay Time	t <sub>d</sub>	V <sub>CC</sub> =3V,V <sub>BE(off)</sub> =-0.5V			35	ns
Delay Time	La	I <sub>C</sub> =10mA,I <sub>B1</sub> =1mA			33	115
Rise Time	+	V <sub>CC</sub> =3V,V <sub>BE(off)</sub> =-0.5V			35	ns
Nise Tillle	t <sub>r</sub>	I <sub>C</sub> =10mA,I <sub>B1</sub> =1mA			33	115
Storage Time		V <sub>CC</sub> =3V,I <sub>C</sub> =10mA			200	
Storage Time	t <sub>s</sub>	I <sub>B1</sub> = I <sub>B2</sub> =1mA			200	ns
Fall Time		V <sub>CC</sub> =3V,I <sub>C</sub> =10mA			F0	
rali illile	t <sub>f</sub>	I <sub>B1</sub> = I <sub>B2</sub> =1mA			50	ns



# Typical Performance Characteristics ( $T_A$ =25 $^{\circ}$ C unless otherwise noted)

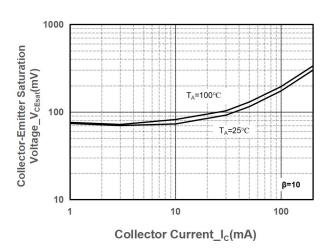




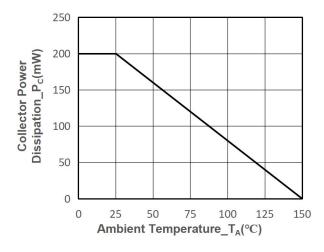
### Collector Current vs. Base-Emitter Voltage

1000 900 Base-Emitter Saturation Voltage\_V<sub>BEsat</sub>(mV) 800 700 600 500 400 300 ß=10 200 100 Collector Current\_Ic(mA)

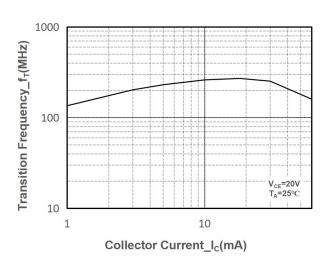
DC Current Gain vs. Collector Current



V<sub>BE(sat)</sub> vs. Collector Current



V<sub>CE(sat)</sub> vs. Collector Current

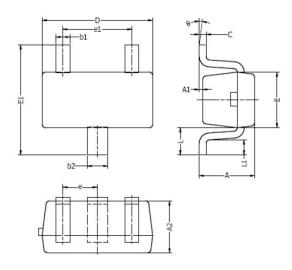


Power derating vs. Ambient temperature

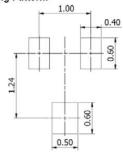
**Transition Frequency vs. Collector Current** 



# Package Information



Typical	Soldering	Pattern:



DIM	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
С	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
е	0.50 TYP.		0.020	TYP.
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016	REF.
L1	0.10	0.30	0.004	0.012
θ	O°	8°	O°	8°

- NOTES:

  1. Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.

  2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

**SOT-523** 



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